

T-37-15

**MAXIMUM RATINGS**

Rating	Symbol	2N869A	2N4453	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	18	18	V <sub>dc</sub>
Collector-Emitter Voltage	V <sub>CES</sub>	25		V <sub>dc</sub>
Collector-Base Voltage	V <sub>CBO</sub>	25	25	V <sub>dc</sub>
Emitter-Base Voltage	V <sub>EBO</sub>	5.0		V <sub>dc</sub>
Collector Current — Continuous	I <sub>C</sub>	200		mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	360 2.06	400 2.29	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C TC = 100°C Derate above 25°C	P <sub>D</sub>	1.2 0.686 6.86	2.0 1.03 11.3	Watts Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	2N869A	2N4453	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	146	97.5	°C/W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	486	585	°C/W

**2N869A**  
 JAN, JTX, JTXV AVAILABLE  
 CASE 22-03, STYLE 1  
 TO-18 (TO-206AA)

**2N4453**  
 JAN, JANTX AVAILABLE  
 CASE 26-03, STYLE 1  
 TO-46 (TO-206AB)

**SWITCHING TRANSISTORS**  
 PNP SILICON

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**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	18	—	V <sub>dc</sub>
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 μAdc, V <sub>BE</sub> = 0)	V <sub>(BR)CES</sub>	25	—	V <sub>dc</sub>
Collector-Emitter Sustaining Voltage(1) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	18	—	V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	25	—	V <sub>dc</sub>
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	—	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 15 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	—	25	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 15 Vdc, V <sub>BE</sub> = 0)	I <sub>CES</sub>	—	10	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	10	nAdc
Base Current (V <sub>CE</sub> = 15 Vdc, V <sub>BE</sub> = 0)	I <sub>B</sub>	—	10	nAdc
<b>ON CHARACTERISTICS(1)</b>				
DC Current Gain (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 0.3 Vdc) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	30 40	— 120	—
(I <sub>C</sub> = 30 mAdc, V <sub>CE</sub> = 0.5 Vdc)		40	120	
(I <sub>C</sub> = 30 mAdc, V <sub>CE</sub> = 0.5 Vdc, T <sub>A</sub> = -55°C) (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)		17 25	— —	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 1.5 mAdc) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 3.0 mAdc) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	— — — —	0.15 0.25 0.2 0.5	V <sub>dc</sub>
Base-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 1.5 mAdc) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 3.0 mAdc) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>BE(sat)</sub>	0.78 0.8 0.85 —	0.98 1.1 1.2 1.7	V <sub>dc</sub>

**ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit	
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Current-Gain — Bandwidth Product(1)(2) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 15\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	400	—	MHz	
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 140\text{ kHz}$ )	$C_{obo}$	—	6.0	pF	
Input Capacitance ( $V_{BE} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 150\text{ kHz}$ )	$C_{ibo}$	—	6.0	pF	
Collector-Base Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	—	6.0	pF	
Emitter-Base Capacitance ( $V_{BE} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{eb}$	—	6.0	pF	
<b>SWITCHING CHARACTERISTICS</b>					
Turn-On Time	$I_C = 30\text{ mAdc}$ , $V_{CC} = 2.0\text{ Vdc}$ 2N869A $I_{B1} = 1.5\text{ mAdc}$ $V_{CC} = 3.0\text{ Vdc}$ 2N4453	$t_{on}$	—	50	ns
Delay Time		$t_d$	—	35	ns
Rise Time		$t_r$	—	20	ns
Turn-Off Time	$I_C = 30\text{ mAdc}$ , $V_{CC} = 2.0\text{ Vdc}$ 2N869A $I_{B1} = I_{B2} = 1.5\text{ mAdc}$ $V_{CC} = 3.0\text{ Vdc}$ 2N4453	$t_{off}$	—	80	ns
Storage Time		$t_s$	—	65	ns
Fall Time		$t_f$	—	20	ns

(1) Pulse Test; Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle = 1.0%.  
 (2)  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

**TYPICAL SWITCHING CHARACTERISTICS**

FIGURE 1 — CAPACITANCE

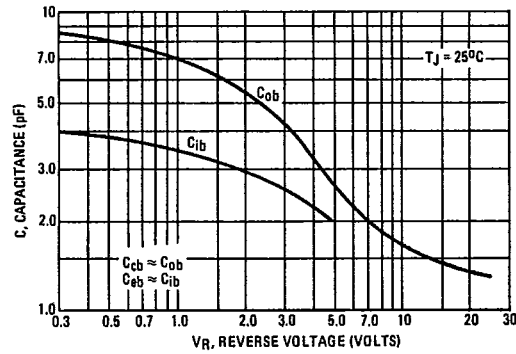


FIGURE 2 — DC CURRENT GAIN

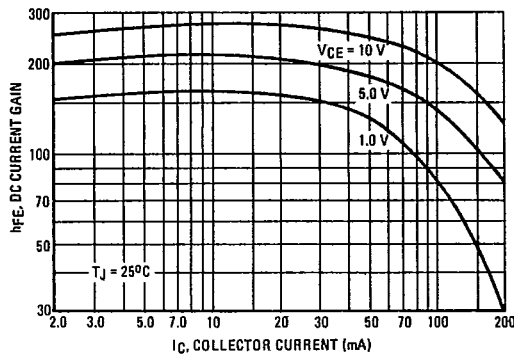


FIGURE 3 — "ON" VOLTAGES

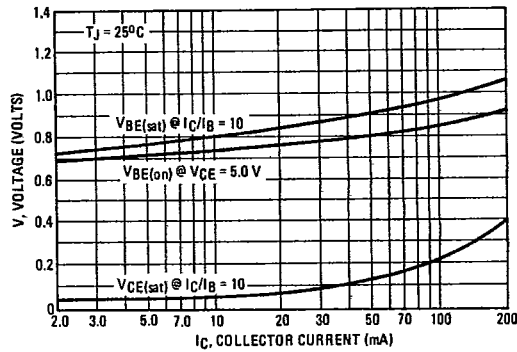


FIGURE 4 — CURRENT-GAIN — BANDWIDTH PRODUCT

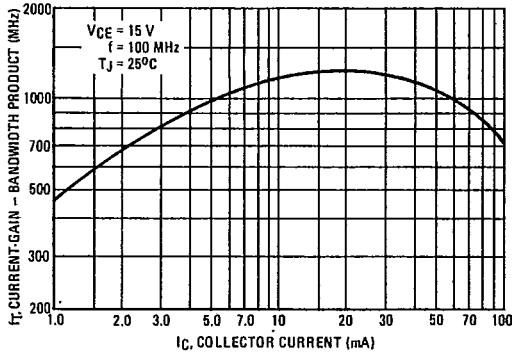
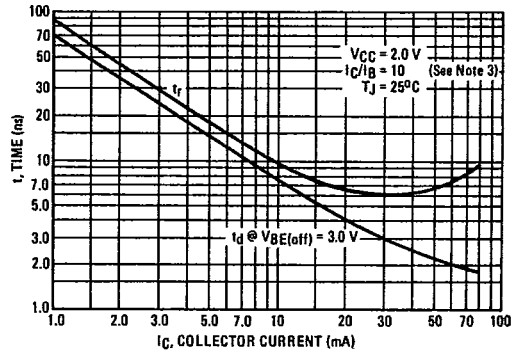


FIGURE 5 — TURN-ON TIME



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FIGURE 6 — TURN-OFF TIME

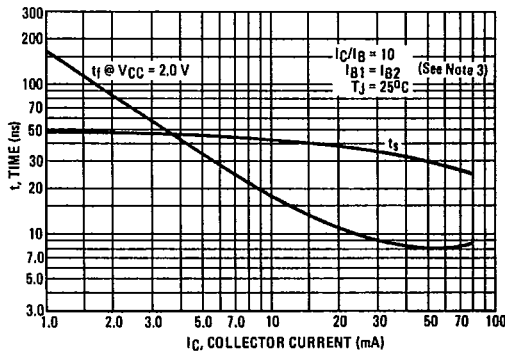


FIGURE 7 — SWITCHING TIME TEST CIRCUIT

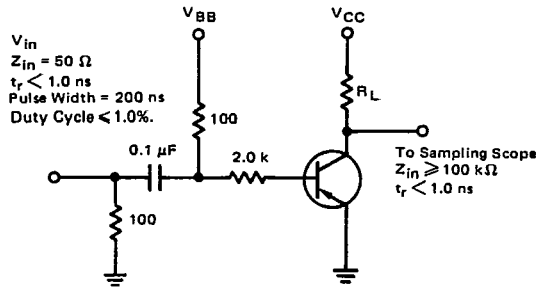


FIGURE 8 — SWITCHING TEST CIRCUIT VALUES

		V <sub>in</sub> Volts	V <sub>BB</sub> Volts	V <sub>CC</sub> Volts	R <sub>L</sub> Ohms	I <sub>C</sub> mA	I <sub>B1</sub> <sup>(4)</sup> mA	I <sub>B2</sub> <sup>(4)</sup> mA
t <sub>on</sub> , t <sub>r</sub> , t <sub>d</sub>	2N869A	-7.0	3.0	2.0	62	30	1.5	—
	2N4453	-7.0	3.0	3.0	91	30	1.5	—
t <sub>off</sub> , t <sub>s</sub> , t <sub>f</sub>	2N869A	+6.0	-4.0	2.0	62	30	1.5	1.5
	2N4453	+6.0	-4.0	3.0	91	30	1.5	1.5

(3) I<sub>C</sub>/I<sub>B</sub> = 10. Switching is shown to reflect current industry practices. Compare the values shown in Figures 1 and 2 @ I<sub>C</sub> = 30 mA to the typical values in the Electrical Characteristics table @ I<sub>C</sub>/I<sub>B</sub> = 20.  
 (4) I<sub>B1</sub> = I<sub>B2</sub> = 3.0 mA @ I<sub>C</sub>/I<sub>B</sub> = 10